

N-Channel 30-V (D-S) MOSFET

PRODUCT SUMMARY	
V_{DS} (V)	30
$R_{DS(on)}$ (Ω) at $V_{GS} = 10$ V	0.003
$R_{DS(on)}$ (Ω) at $V_{GS} = 4.5$ V	0.004
I_D (A)	120
Configuration	Single

FEATURES

- TrenchFET® Power MOSFET
- 100 % R_g and UIS Tested
- Compliant to RoHS Directive 2011/65/EU

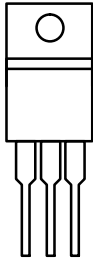


RoHS
COMPLIANT

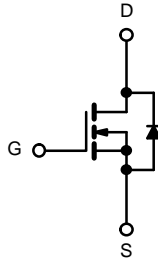
APPLICATIONS

- OR-ing
- Server
- DC/DC

TO-220AB



G D S
Top View



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS ($T_A = 25$ °C, unless otherwise noted)				
Parameter	Symbol	Limit	Unit	
Drain-Source Voltage	V_{DS}	30	V	
Gate-Source Voltage	V_{GS}	± 20		
Continuous Drain Current ($T_J = 175$ °C)	I_D	$T_C = 25$ °C	120	A
		$T_C = 70$ °C	60 ^e	
		$T_A = 25$ °C	28.8 ^{b, c}	
		$T_A = 70$ °C	19 ^{b, c}	
Pulsed Drain Current	I_{DM}	380		
Avalanche Current Pulse	I_{AS}	36	V	
Single Pulse Avalanche Energy				
Continuous Source-Drain Diode Current	I_S	$T_C = 25$ °C	90 ^{a, e}	A
		$T_A = 25$ °C	3.13 ^{b, c}	
Maximum Power Dissipation	P_D	$T_C = 25$ °C	250 ^a	W
		$T_C = 70$ °C	175	
		$T_A = 25$ °C	3.75 ^{b, c}	
		$T_A = 70$ °C	2.63 ^{b, c}	
Operating Junction and Storage Temperature Range	T_J, T_{stg}	- 55 to 175	°C	

THERMAL RESISTANCE RATINGS					
Parameter	Symbol	Typ.	Max.	Unit	
Maximum Junction-to-Ambient ^{b, d}	R_{thJA}	32	40	°C/W	
Maximum Junction-to-Case	R_{thJC}	0.5	0.6		

Notes:

a. Based on $T_C = 25$ °C.

b. Surface mounted on 1" x 1" FR4 board.

c. $t = 10$ sec.

d. Maximum under steady state conditions is 90 °C/W.

e. Calculated based on maximum junction temperature. Package limitation current is 90 A.

SPECIFICATIONS ($T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted)						
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$	30			V
V_{DS} Temperature Coefficient	$\Delta V_{DS}/T_J$	$I_D = 250\text{ }\mu\text{A}$		35		mV/ $^\circ\text{C}$
$V_{GS(th)}$ Temperature Coefficient	$\Delta V_{GS(th)}/T_J$			-7.5		
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	1.0		2.5	V
Gate-Source Leakage	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 30\text{ V}, V_{GS} = 0\text{ V}$			1	μA
		$V_{DS} = 30\text{ V}, V_{GS} = 0\text{ V}, T_J = 55\text{ }^\circ\text{C}$			10	
On-State Drain Current ^a	$I_{D(on)}$	$V_{DS} \geq 5\text{ V}, V_{GS} = 10\text{ V}$	90			A
Drain-Source On-State Resistance ^a	$R_{DS(on)}$	$V_{GS} = 10\text{ V}, I_D = 28.8\text{ A}$		0.003		Ω
		$V_{GS} = 4.5\text{ V}, I_D = 27\text{ A}$		0.004		
Forward Transconductance ^a	g_{fs}	$V_{DS} = 15\text{ V}, I_D = 28.8\text{ A}$		160		S
Dynamic^b						
Input Capacitance	C_{iss}	$V_{DS} = 15\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$		3100		pF
Output Capacitance	C_{oss}			725		
Reverse Transfer Capacitance	C_{rss}			370		
Total Gate Charge	Q_g	$V_{DS} = 15\text{ V}, V_{GS} = 10\text{ V}, I_D = 28.8\text{ A}$		171	257	nC
				81.5	123	
Gate-Source Charge	Q_{gs}	$V_{DS} = 15\text{ V}, V_{GS} = 4.5\text{ V}, I_D = 28.8\text{ A}$		34		
Gate-Drain Charge	Q_{gd}			29		
Gate Resistance	R_g	$f = 1\text{ MHz}$		1.4	2.1	Ω
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 15\text{ V}, R_L = 0.625\text{ }\Omega$ $I_D \cong 24\text{ A}, V_{GEN} = 10\text{ V}, R_g = 1\text{ }\Omega$		18	27	ns
Rise Time	t_r			11	17	
Turn-Off Delay Time	$t_{d(off)}$			70	105	
Fall Time	t_f			10	15	
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 15\text{ V}, R_L = 0.67\text{ }\Omega$ $I_D \cong 22.5\text{ A}, V_{GEN} = 4.5\text{ V}, R_g = 1\text{ }\Omega$		55	83	
Rise Time	t_r			180	270	
Turn-Off Delay Time	$t_{d(off)}$			55	83	
Fall Time	t_f			12	18	
Drain-Source Body Diode Characteristics						
Continuous Source-Drain Diode Current	I_S	$T_C = 25\text{ }^\circ\text{C}$			90	A
Pulse Diode Forward Current ^a	I_{SM}				90	
Body Diode Voltage	V_{SD}	$I_S = 22\text{ A}$		0.8	1.2	V
Body Diode Reverse Recovery Time	t_{rr}	$I_F = 20\text{ A}, di/dt = 100\text{ A}/\mu\text{s}, T_J = 25\text{ }^\circ\text{C}$		52	78	ns
Body Diode Reverse Recovery Charge	Q_{rr}			70.2	105	nC
Reverse Recovery Fall Time	t_a			27		ns
Reverse Recovery Rise Time	t_b			25		

Notes:

- a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.
 b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Output Characteristics



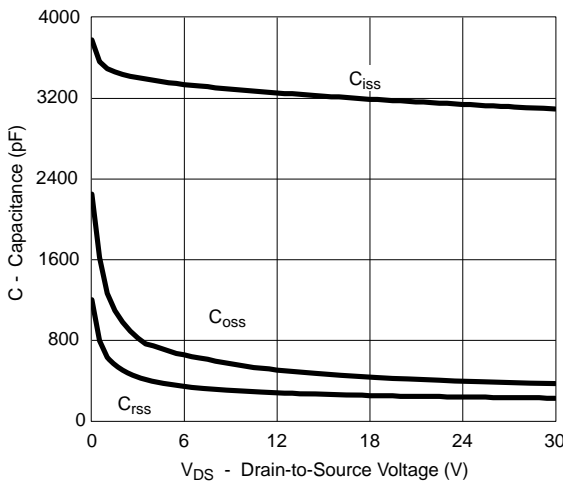
Transfer Characteristics



Transconductance



$R_{DS(on)}$ vs. Drain Current



Capacitance



Gate Charge

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



On-Resistance vs. Junction Temperature



Forward Diode Voltage vs. Temperature



$R_{DS(on)}$ vs. V_{GS} vs. Temperature

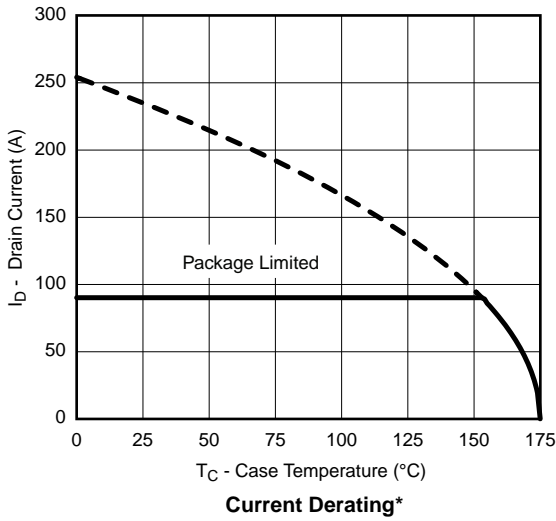


Threshold Voltage



Safe Operating Area, Junction-to-Ambient
* $V_{GS} >$ minimum V_{GS} at which $r_{DS(on)}$ is specified

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



*The power dissipation P_D is based on T_{J(max)} = 175 °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.



TO-220AB



DIM.	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	4.25	4.65	0.167	0.183
b	0.69	1.01	0.027	0.040
b(1)	1.20	1.73	0.047	0.068
c	0.36	0.61	0.014	0.024
D	14.85	15.49	0.585	0.610
E	10.04	10.51	0.395	0.414
e	2.41	2.67	0.095	0.105
e(1)	4.88	5.28	0.192	0.208
F	1.14	1.40	0.045	0.055
H(1)	6.09	6.48	0.240	0.255
J(1)	2.41	2.92	0.095	0.115
L	13.35	14.02	0.526	0.552
L(1)	3.32	3.82	0.131	0.150
Ø P	3.54	3.94	0.139	0.155
Q	2.60	3.00	0.102	0.118

ECN: X12-0208-Rev. N, 08-Oct-12
DWG: 5471

Notes

* M = 1.32 mm to 1.62 mm (dimension including protrusion)
Heatsink hole for HVM

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